MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

Silicon Hot-Carrier Diodes

Schottky Barrier Diodes

These devices are designed primarily for high-efficiency UHF and VHF detector applications. They are readily adaptable to many other fast switching RF and digital applications. They are supplied in an inexpensive plastic package for low-cost, high-volume consumer and industrial/commercial requirements. They are also available in a Surface Mount package.

Features

- Extremely Low Minority Carrier Lifetime 15 ps (Typ)
- Very Low Capacitance 1.5 pF (Max) @ V_R = 15 V
- Low Reverse Leakage I_R = 13 nAdc (Typ) MBD301, MMBD301
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Forward Current (DC)	ΙF	200 (Max)	mA
Total Device Dissipation (a) T _A = 25°C MBD301G MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G Derate above 25°C MBD301G MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G	P _F	280 200 2.8 2.0	MW mW/°C
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

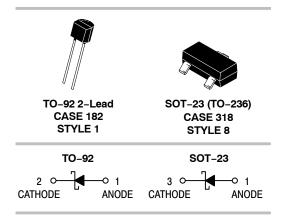
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



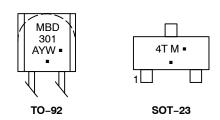
ON Semiconductor®

www.onsemi.com

30 VOLTS SILICON HOT-CARRIER DETECTOR AND SWITCHING DIODES



MARKING DIAGRAMS



A = Assembly Location

/ = Year

W = Work Week

4T = Device Code (SOT-23)

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I _R = 10 μA)	V _{(BR)R}	30	-	-	V
Total Capacitance (V _R = 15 V, f = 1.0 MHz) Figure 1	C _T	-	0.9	1.5	pF
Reverse Leakage (V _R = 25 V) Figure 3	I _R	-	13	200	nAdc
Forward Voltage (I _F = 1.0 mAdc) Figure 4	V _F	-	0.38	0.45	Vdc
Forward Voltage (I _F = 10 mAdc) Figure 4	V _F	-	0.52	0.6	Vdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBD301G	TO-92 (Pb-Free)	5,000 Units / Bulk
MMBD301LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBD301LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBD301G, MMBD301LT1G, MMBD301LT3G, SMMBD301LT3G

TYPICAL ELECTRICAL CHARACTERISTICS

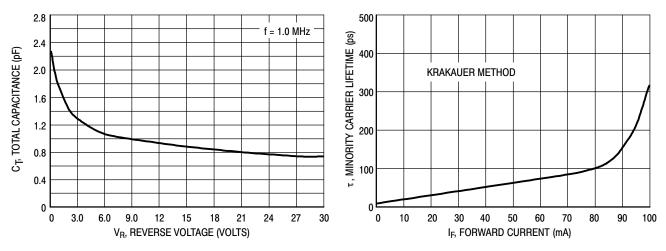


Figure 1. Total Capacitance

Figure 2. Minority Carrier Lifetime

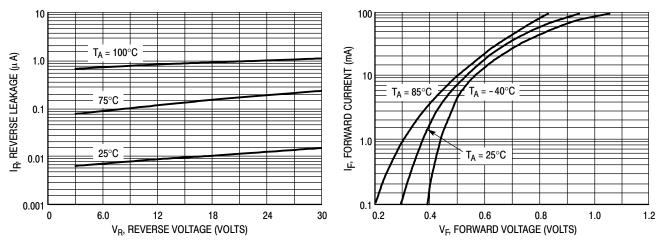


Figure 3. Reverse Leakage

Figure 4. Forward Voltage

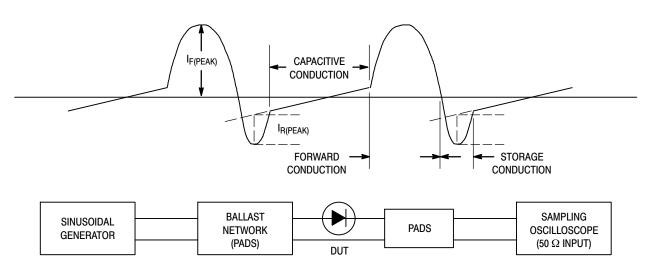
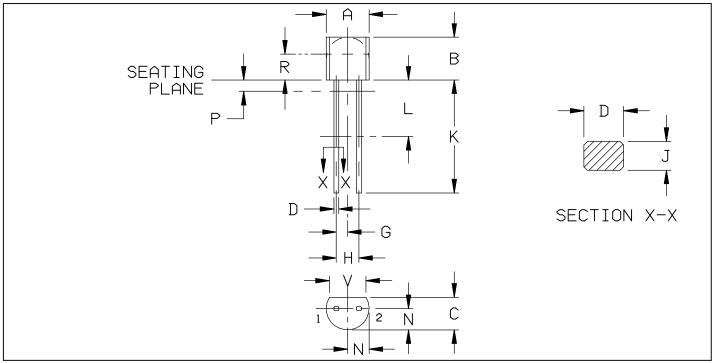


Figure 5. Krakauer Method of Measuring Lifetime





	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A	4. 45	5.21	0.175	0.205
В	4.32	5.33	0.170	0.210
С	3.18	4.19	0.125	0.165
D	0.407	0.533	0.016	0.021
G	1.27	BSC	0.050	BSC
Н	2.54	BSC	0.100) BSC
J	0.36	0.41	0.014	0.016
K	12.70		0.500	
L	6. 35		0.250	
N	2.03	2.66	0.080	0.105
Р		1.27		0.050
R	2. 93		0.115	
V	3. 43		0.135	

CASE NO.	182-06
STATUS	TO-226AC
NEW STD	
USED ON	VL225 THRU 289

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. CONTOUR OF PACKAGE BEYOND ZONE R IS UNCONTROLLED.
- 4. LEAD DIM IS UNCONTROLLED IN P AND BEYOND DIM K MINIMUM.
- 5. 182-01 THRU -04 OBSOLETE, NEW STANDARD 182-06.

STYLE 1: STYLE 2:

PIN 1. ANODE PIN 1. CATHODE

2. CATHODE

2. ANODE

STYLE 3: STYLE 4: OBSOLETE

PIN 1. MAIN TERM 1

2. MAIN TERM 2

STYLE 5:

PIN 1. INPUT

2. OUTPUT

DOC. NO. 98ASB42118B PAGE NO. 2 of 2

ISSUE	REVISION	COORD/ DATE
J	SH 1: DIM "F" WAS407482, .016019. REQ BY T. GRINTER.	FB 27 JAN1998
K	SH 1 : DIMENSIONS "D", "F" WERE 0.56, 0.022. REQ BY T. GRINTER.	FB 10 FEB 1998
L	DELETED DIM "F" AND REVISED NOTE 4. REQ BY T. GRINTER.	FB 14 APR 1998

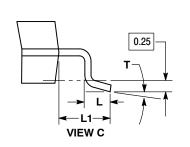


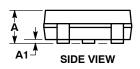
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

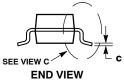
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

PROT	RUSIONS, OR GATE BURRS.	
		T

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	ANODE	CATHODE	ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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